

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)	ATTY. DOCKET NO. 12007-0074	SERIAL NO. 10/580,653
	APPLICANT Wolfgang STOLZ et al.	
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO PART.
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/KQ/	1.	C. Ellmers, et al., "GaAs-based VCSEL-structures with strain-compensated (GaIn)As/Ga(PAs)-MQWH active regions grown by using TBAs and TBP", Journal of Crystal Growth 195 (1998) 630-636
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EXAMINER /Kevin Quinto/	DATE CONSIDERED 01/02/2008
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.